**Pb Free Product** 



# NCEP01T11

#### **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The NCEP01T11 uses Super Trench technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

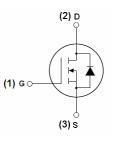
- V<sub>DS</sub> =100V,I<sub>D</sub> =108A  $R_{DS(ON)}$ =5.7m $\Omega$  (typical) @  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

#### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



#### Schematic diagram



Marking and pin assignment



TO-220-3L top view

#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP01T11	NCEP01T11	TO-220-3L	-	-	-

#### Absolute Maximum Ratings (T<sub>C</sub>=25°Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous (Silicon Limited)	I <sub>D</sub>	108	Α
Drain Current-Continuous (Package Limited)	I <sub>D</sub>	108	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	78	Α
Pulsed Drain Current	I <sub>DM</sub>	380	Α
Maximum Power Dissipation	P <sub>D</sub>	160	W
Derating factor		1.1	W/°C



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# NCEP01T11

Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	676	mJ			
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 175	$^{\circ}$ C			
Thermal Characteristic						

Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	0.94	°C/W
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#### Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	<u> </u>					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20 $V$ , $V_{DS}$ =0 $V$	-	-	±100	nA
On Characteristics (Note 3)	<u> </u>					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.5	-	4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =50A	-	5.7	6.5	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =50A	40	-	-	S
Dynamic Characteristics (Note4)	<u>.                                      </u>		•			
Input Capacitance	C <sub>lss</sub>	\/ -50\/\/ -0\/	-	4300	-	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =50V, $V_{GS}$ =0V, F=1.0MHz	-	790	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	r=1.0lvlm2	-	47	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	13	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =50 $V$ , $I_D$ =50 $A$	-	58	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{G}$ =4.7 $\Omega$	-	39	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Qg	\/ -50\/  -50A	-	60		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =50V, $I_{D}$ =50A, $V_{GS}$ =10V	-	21		nC
Gate-Drain Charge	$Q_{gd}$	VGS-10V	-	11		nC
Drain-Source Diode Characteristics	·		•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =108A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	108	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = I_S$	-	60		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	140		nC

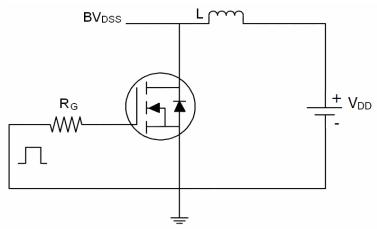
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=50V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

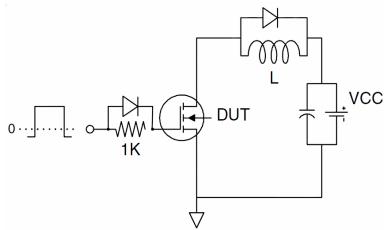


#### **Test Circuit**

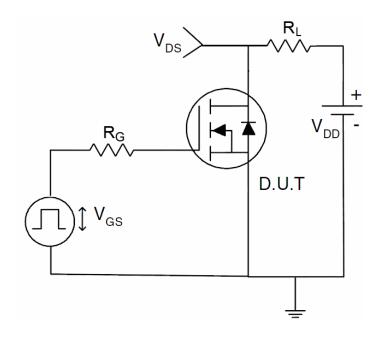
#### 1) E<sub>AS</sub> test Circuit



#### 2) Gate charge test Circuit

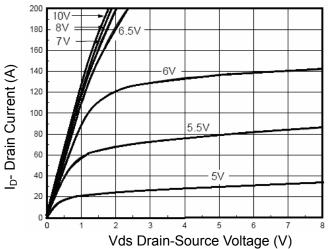


#### 3) Switch Time Test Circuit

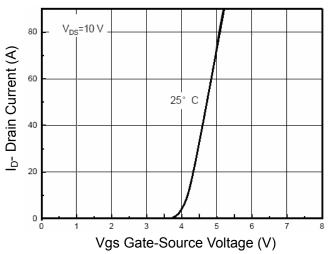








**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

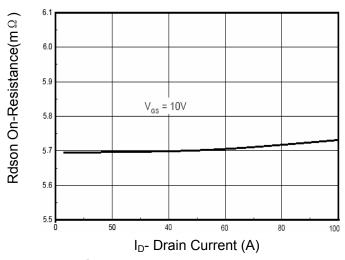


Figure 3 Rdson- Drain Current

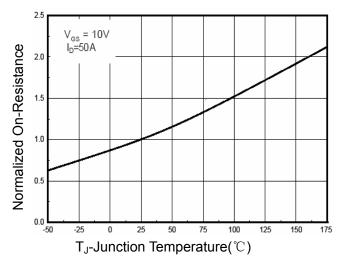


Figure 4 Rdson-JunctionTemperature

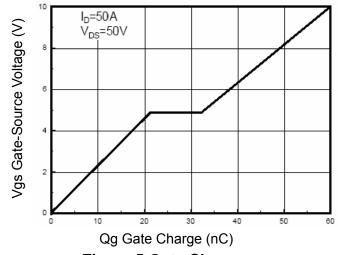


Figure 5 Gate Charge

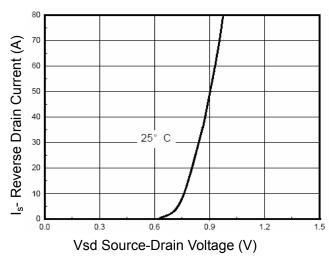


Figure 6 Source- Drain Diode Forward



C Capacitance (pF)

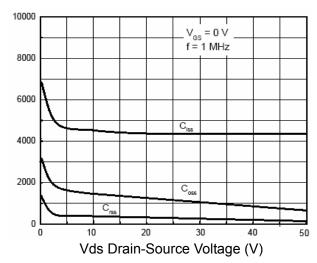


Figure 7 Capacitance vs Vds

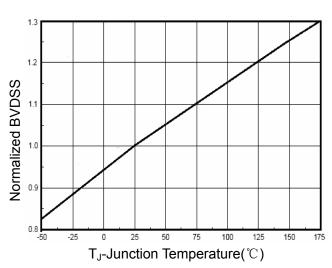
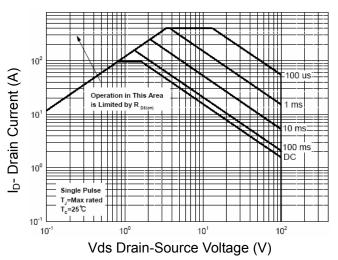


Figure 9 BV<sub>DSS</sub> vs Junction Temperature



**Figure 8 Safe Operation Area** 

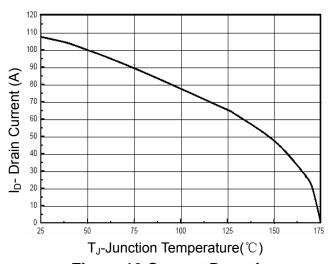


Figure 10 Current De-rating

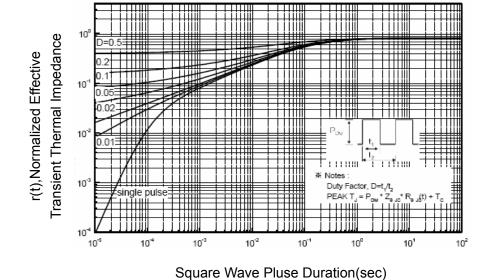
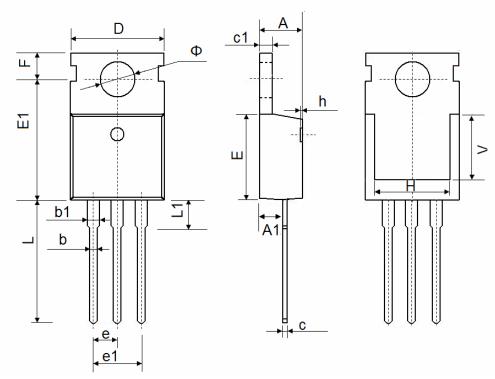


Figure 11 Normalized Maximum Transient Thermal Impedance

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### **TO-220-3L Package Information**



Comphal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500	7.500 REF.		REF.	
Ф	3.400	3.800	0.134	0.150	



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